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(54) Title: **PROCESS FOR PREPARING SILICA OR SILICA-BASED THICK VITREOUS FILMS ACCORDING TO THE SOL-GEL TECHNIQUE AND THICK FILMS THEREBY OBTAINED**

(57) Abstract

It is described a sol-gel process allowing the preparation, on a substrate, of glassy films of silicon oxide or mixed oxides based on silicon oxide, of thickness above 1 micrometer, generally between 2 and 20 micrometers, and characterised by absence of defects, that turn out to be particularly suitable as waveguides in flat optical devices.

